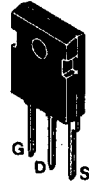
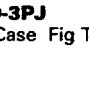




# Power MOSFETS (cont'd)

ECG Type	Description and Application	Transconductance gfs $\mu$ mhos	Drain to Source Breakdown Voltage BV <sub>DSS</sub>	Gate to Source Breakdown Voltage BV <sub>GS</sub>	Continuous Drain Current I <sub>D</sub> Amps	Gate to Source Threshold Voltage V <sub>GS</sub> (th)	Drain to Source Resistance r <sub>DS</sub> (on) Ohms	Input Cap C <sub>iss</sub> pf	Device Dissipation @T <sub>C</sub> =25° C P <sub>D</sub> Watts	Package
										Case/Fig./Basing
ECG2920 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	25 Min	60 Min	±20 Max*	70	4 Max	.014 Max	4000 Typ	200 Max	<b>TO-247</b> Fig. T48-4 
ECG2375 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	13 Min	100 Min	±20 Max*	40	4 Max	.055 Max	2000 Typ	180 Max	
ECG2376 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	13 Min	200 Min	±20 Max*	30	4 Max	.085 Max	2000 Typ	180 Max	
ECG2921 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	250 Min	±20 Max*	15	4 Max	.28 Max	1400 Typ	150 Max	
										td(off) = 50 ns, td(on) = 20 ns, tf = 30 ns, tr = 60 ns
ECG2922 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	400 Min	±20 Max*	16	4 Max	.3 Max	2900 Max	180 Max	
										td(off) = 140 ns, td(on) = 40 ns, tf = 50 ns, tr = 115 ns
ECG2923 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	500 Min	±20 max*	9	4 Max	.85 Max	1000 Typ	180 Max	
										td(off) = 50 ns, td(on) = 20 ns, tf = 30 ns, tr = 30 ns
ECG2924 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	20 Min	600 Min	±20 max*	7	4 Max	1.3 Max	1000 Typ	180 Max	<b>TO-3PJ</b> Alt. Case Fig T48-1 

# Logic Level MOSFET†

ECG Type	Description and Application	Transconductance gfs $\mu$ mhos	Drain to Source Breakdown Voltage BV <sub>DSS</sub>	Gate to Source Breakdown Voltage BV <sub>GS</sub>	Continuous Drain Current I <sub>D</sub> Amps	Gate to Source Threshold Voltage V <sub>GS</sub> (th)	Drain to Source Resistance r <sub>DS</sub> (on) Ohms	Input Cap C <sub>iss</sub> pf	Device Dissipation @T <sub>C</sub> =25° C P <sub>D</sub> Watts	Package
										Case/Fig./Basing
ECG2984 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	60 Min	±15 Max*	15	2.5 Max	.15 Max	500 Max	70 Max	<b>TO-220</b> Fig. T41 
ECG2985 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	10 Min	60 Min	±15 Max*	30	2.5 Max	.055 Max	1300 Max	100 Max	
ECG2986 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	17 Min	60 Min	±15 Max	50	2.5 Max	.028 Max	2600 Max	150 Max	
ECG2987 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	10 Min	100 Min	±15 Max*	20	2.5 Max	.12 Max	1500 Max	100 Max	
										td(off) = 80 ns, td(on) = 60 ns, tf = 80 ns, tr = 160 ns
ECG2980 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	60 Min	±10 Max*	7	2 Max	.2 Max	400 Typ	25 Max	
										td(off) = 20 ns, td(on) = 15 ns, tf = 30 ns, tr = 120 ns
ECG2981 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	4 Min	100 Min	±10 Max*	7	2 Max	.27 Max	490 Typ	42 Max	<b>TO-126N</b> Fig. T45-5 

\*Warning - Exceeding BV<sub>GS</sub> maximum will result in permanent damage to the gate region oxide layer.

▲ Refer to MOSFET Handling Precautions - Page 1 - 34

† Logic Level MOSFETS are fully enhanced when 5V is applied to the gate.

Package Outlines - See Page 1-91